## TOSHIBA Field Effect Transistor Silicon N Channel Junction Type

## 2SK367

For Audio, High Voltage Amplifier and Constant Current Applications

- High breakdown voltage: $\mathrm{VGDS}_{\mathrm{GDS}}=-100 \mathrm{~V}(\mathrm{~min})$
- High input impedance: $\mathrm{I}_{\mathrm{GSS}}=-1.0 \mathrm{nA}(\max )\left(\mathrm{V}_{\mathrm{GS}}=-80 \mathrm{~V}\right)$
- Small package


## Absolute Maximum Ratings ( $\mathbf{T a}=\mathbf{2 5}{ }^{\circ} \mathrm{C}$ )

| Characteristics | Symbol | Rating | Unit |
| :--- | :---: | :---: | :---: |
| Gate-drain voltage | $\mathrm{V}_{\mathrm{GDS}}$ | -100 | V |
| Gate current | $\mathrm{I}_{\mathrm{G}}$ | 10 | mA |
| Drain power dissipation | $\mathrm{P}_{\mathrm{D}}$ | 200 | mW |
| Junction temperature | $\mathrm{T}_{\mathrm{j}}$ | 125 | ${ }^{\circ} \mathrm{C}$ |
| Storage temperature range | $\mathrm{T}_{\text {stg }}$ | $-55 \sim 125$ | ${ }^{\circ} \mathrm{C}$ |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual Unit: mm


Weight: 0.13 g (typ.)

Electrical Characteristics ( $\mathbf{T a}=\mathbf{2 5}{ }^{\circ} \mathrm{C}$ )

| Characteristics | Symbol | Test Condition | Min | Typ. | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Gate cut-off current | IGSS | $\mathrm{V}_{\mathrm{GS}}=-80 \mathrm{~V}, \mathrm{~V}_{\mathrm{DS}}=0$ | - | - | -1.0 | nA |
| Gate-drain breakdown voltage | $V$ (BR) GDS | $\mathrm{V}_{\mathrm{DS}}=0, \mathrm{I}_{\mathrm{G}}=-100 \mu \mathrm{~A}$ | -100 | - | - | V |
| Drain current | IDSs <br> (Note) | $V_{D S}=10 \mathrm{~V}, \mathrm{~V}_{\mathrm{GS}}=0$ | 0.6 | - | 6.5 | mA |
| Gate-source cut-off voltage | $\mathrm{V}_{\mathrm{GS}}$ (OFF) | $\mathrm{V}_{\mathrm{DS}}=10 \mathrm{~V}, \mathrm{I}_{\mathrm{D}}=0.1 \mu \mathrm{~A}$ | -0.4 | - | -3.5 | V |
| Forward transfer admittance | $\left\|Y_{\text {fs }}\right\|$ | $\mathrm{V}_{\mathrm{DS}}=10 \mathrm{~V}, \mathrm{~V}_{\mathrm{GS}}=0, \mathrm{f}=1 \mathrm{kHz}$ | 1.5 | 4.6 | - | mS |
| Input capacitance | Ciss | $\mathrm{V}_{\mathrm{DS}}=10 \mathrm{~V}, \mathrm{~V}_{\mathrm{GS}}=0, \mathrm{f}=1 \mathrm{MHz}$ | - | 13 | - | pF |
| Reverse transfer capacitance | $\mathrm{C}_{\text {rss }}$ | $\mathrm{V}_{\mathrm{DS}}=10 \mathrm{~V}, \mathrm{I}_{\mathrm{D}}=0, \mathrm{f}=1 \mathrm{MHz}$ | - | 3 | - | pF |
| Noise figure | NF | $\begin{aligned} & V_{D S}=10 \mathrm{~V}, \mathrm{~V}_{\mathrm{GS}}=0, R_{G}=100 \mathrm{k} \Omega, \\ & \mathrm{f}=100 \mathrm{~Hz} \end{aligned}$ | - | 0.5 | - | dB |

Note: IDSS classification $\mathrm{O}: 0.6 \sim 1.4 \mathrm{~mA}, \mathrm{Y}: 1.2 \sim 3.0 \mathrm{~mA}, \mathrm{GR}: 2.6 \sim 6.5 \mathrm{~mA}$



$\left|\mathrm{Y}_{\mathrm{fS}}\right|-\mathrm{I}_{\mathrm{DSS}}$




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